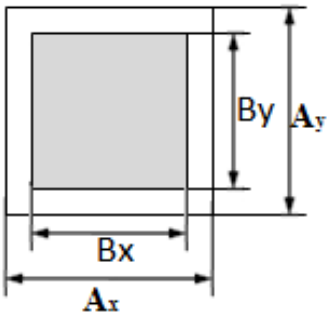


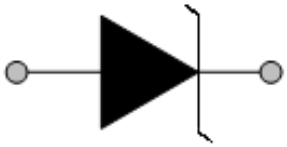

**Mechanical date:** $A_x=A_y$=260um
Bx=By=175um

**Schematic and pinning diagram**

**Chip thickness:** 635+/-20um without griding
**Scribe Line width** - 50um.
**Top Metal:** a) AL with Ti under layer metallization for wire bond, thickness 2,2-2,4um.
b) Ti-Ni-Ag for soldering
**Back side - Anode:** without metallization
**Top Side (Cathode)** - pin 1, **Back Side (Anode)** - pin 2.
**Sampling testing:** no bad dice inking;
guaranteed good dice quantity≥93%.

## Limiting values

| Parameter | Symbol | Conditions | Value | Unit |
|---|---|---|---|---|
| Reverse Stand-off voltage | $V_{RWM}$ | | 5,0. | V |
| Peak Pulse Power | $P_{pp}$ | $t_p$= 8/20uS | 81* | W |
| Peak Pulse Current | $I_{pp}$ | $t_p$= 8/20uS | 6.5* | A |
| Electrostatic Discharge | $V_{ESD}$ | IEC 61000-4-2, level 4. | > +/-10,0 (Contact); > +/-15,0 (Air). | kV |
| Max.junction temperature | $T_j$ | | +150 | ºC |

## Characteristics **(Ta=25ºC)**

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| $I_R$ | Diode reverse leakage current. | V=±5 V | - | - | 0,9 | uA |
| $V_{BR}$ | Breakdown voltage. | $I_R$=1mA | 6.3 | - | 7.3 | V |
| $C_j$ | Diode capacitance . | f=1MHz, $V_{dc}$=0 V. | - | 55 | 70 | pF |
| $V_{CL}$ | Clamping voltage | $I_{pp}$=6,5A; $t_p$= 8/20uS. | - | - | 12,5* | V |

*- For Device testing